

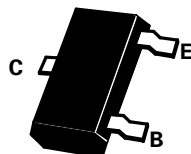
SOT23 PNP SILICON PLANAR SMALL SIGNAL TRANSISTOR

ISSUE 3 – FEBRUARY 1996

FMMTA70

PARTMARKING DETAIL – FMMTA70 – 2CZ

COMPLIMENTARY TYPE – FMMTA20



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-4	V
Continuous Collector Current	I_C	-100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40		V	$I_C=-1mA, I_B=0$
Base-Emitter Breakdown Voltage	$V_{(BR)EBO}$	-4		V	$I_E=-100\mu A, I_C=0$
Collector Base Cut-Off Current	I_{CBO}		-100	nA	$V_{CB}=-30V, I_E=0$
Static Forward Current Transfer Ratio	h_{FE}	40	400		$I_C=-5mA, V_{CE}=-10V^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.25	V	$I_C=-10mA, I_B=-1mA^*$
Transition Frequency	f_T	125		MHz	$I_C=-5mA, V_{CE}=-10V$ $f=100MHz$
Output Capacitance	C_{obo}		4	pF	$V_{CB}=-10V, I_E=0, f=100KHz$

*Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device